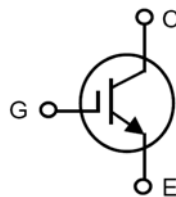


High Voltage XPT™ IGBT

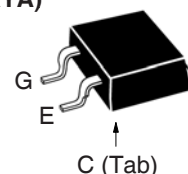
IXYA8N250CHV IXYH8N250CHV

$$\begin{aligned} V_{CES} &= 2500V \\ I_{C110} &= 8A \\ V_{CE(sat)} &\leq 4.0V \\ t_{fi(typ)} &= 86ns \end{aligned}$$

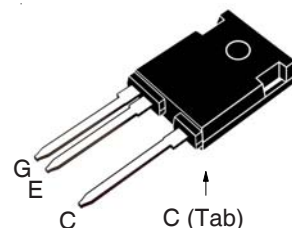


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	2500	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	29	A
I_{C110}	$T_C = 110^\circ\text{C}$	8	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	70	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 15\Omega$	$I_{CM} = 32$	A
	Clamped Inductive Load	1500	V
P_C	$T_C = 25^\circ\text{C}$	280	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight	TO-263HV	2.5	g
	TO-247HV	6.0	g

TO-263HV (IXYA)



TO-247HV (IXYH)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			10 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 8A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$	3.35 4.75	4.00	V V

Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values

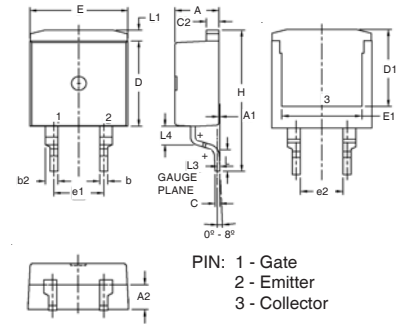
		Min.	Typ.	Max.
g_{fs}	$I_C = 8A, V_{CE} = 10V, \text{Note 1}$	5.4	9.0	S
R_{Gi}	Gate Input Resistance		11	Ω
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$		936	pF
C_{oes}			57	pF
C_{res}			14	pF
$Q_{g(on)}$	$I_C = 8A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		45	nC
Q_{ge}			6	nC
Q_{gc}			21	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 8A, V_{GE} = 15V$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 15\Omega$ Note 2		11	ns
t_{ri}			5	ns
E_{on}			2.60	mJ
$t_{d(off)}$			180	ns
t_{fi}			86	ns
E_{off}			1.07	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 8A, V_{GE} = 15V$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 15\Omega$ Note 2		12	ns
t_{ri}			12	ns
E_{on}			3.70	mJ
$t_{d(off)}$			200	ns
t_{fi}			128	ns
E_{off}			1.20	mJ
R_{thJC}				0.53 $^\circ\text{C/W}$
R_{thCS}	TO-247HV		0.21	$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-263HV Outline


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200	BSC	5.08	BSC
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010	BSC	0.254	BSC
(L4)	.071	.087	1.80	2.20

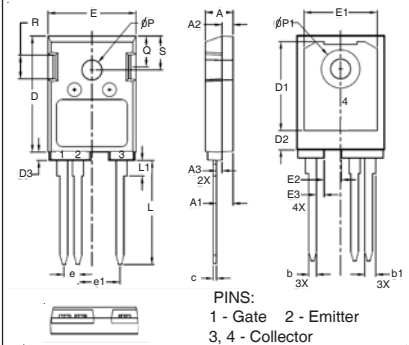
TO-247HV Outline


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

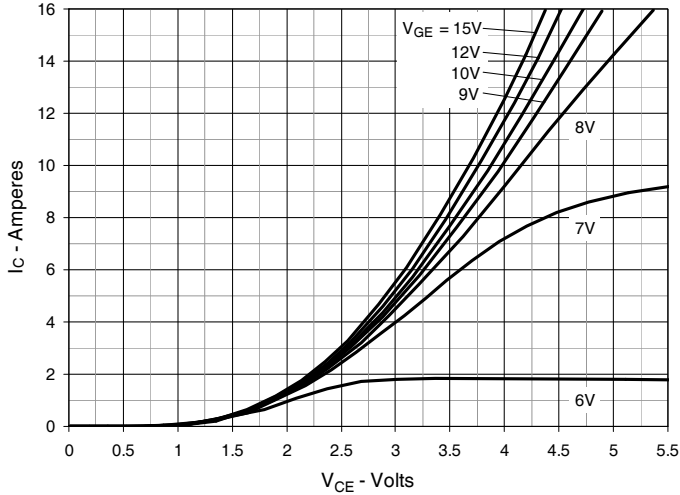


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

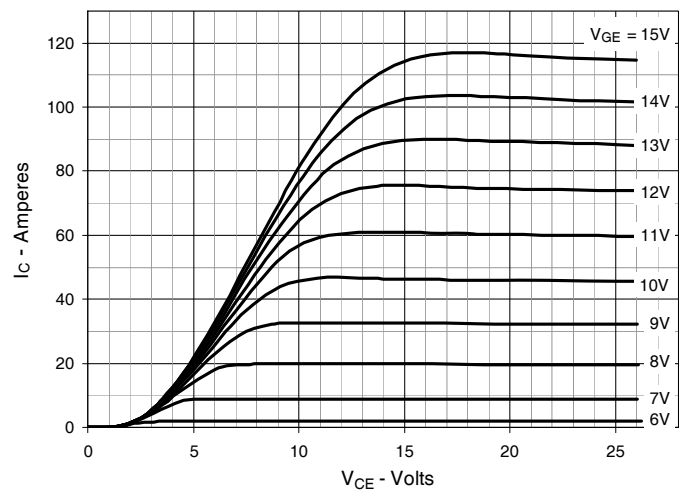


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

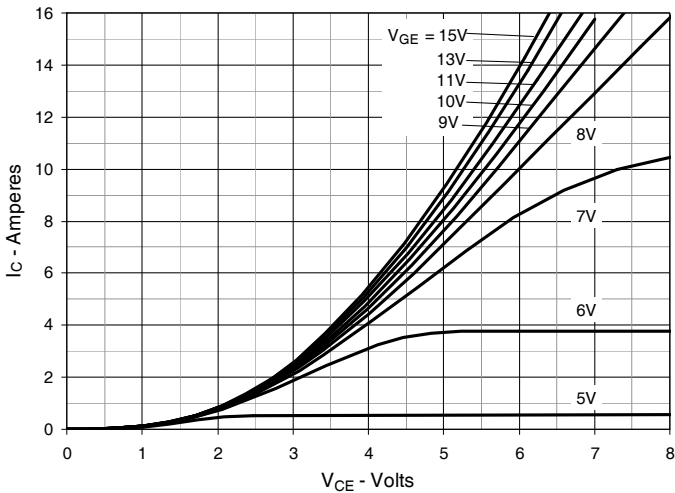


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

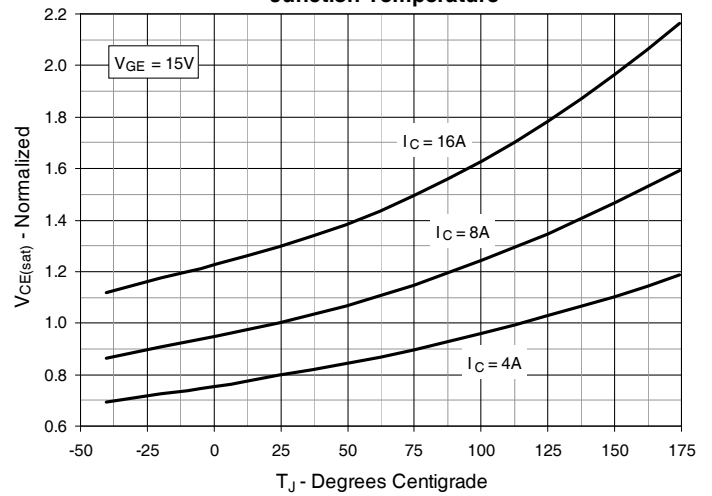


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

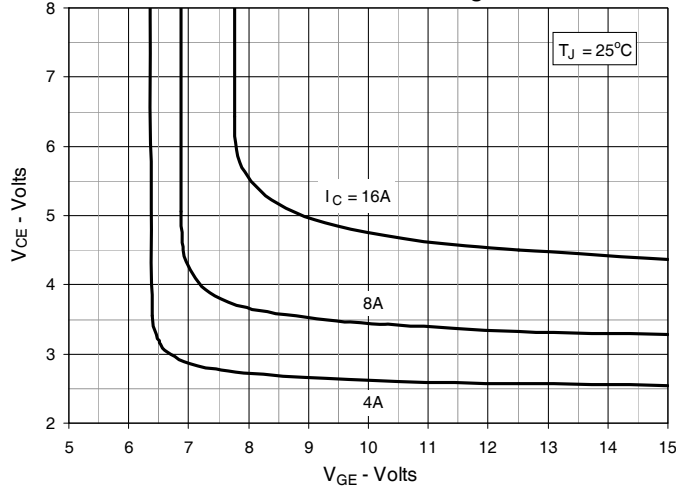


Fig. 6. Input Admittance

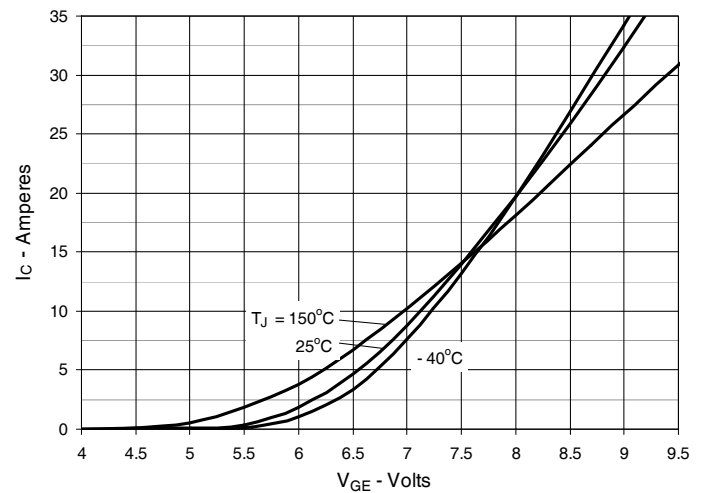


Fig. 7. Transconductance

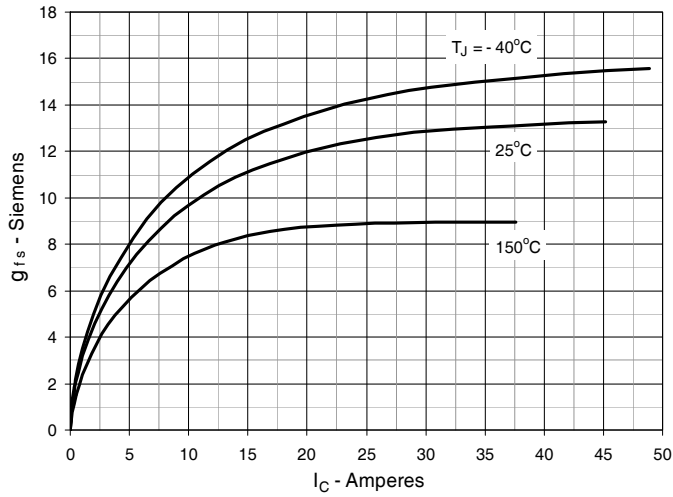


Fig. 8. Gate Charge

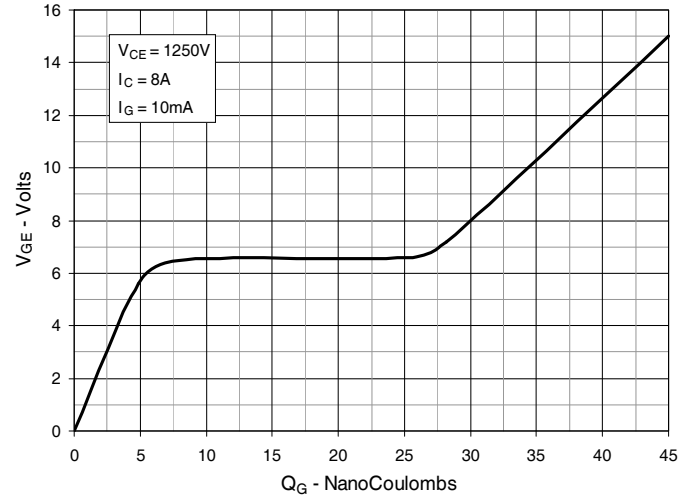


Fig. 9. Capacitance

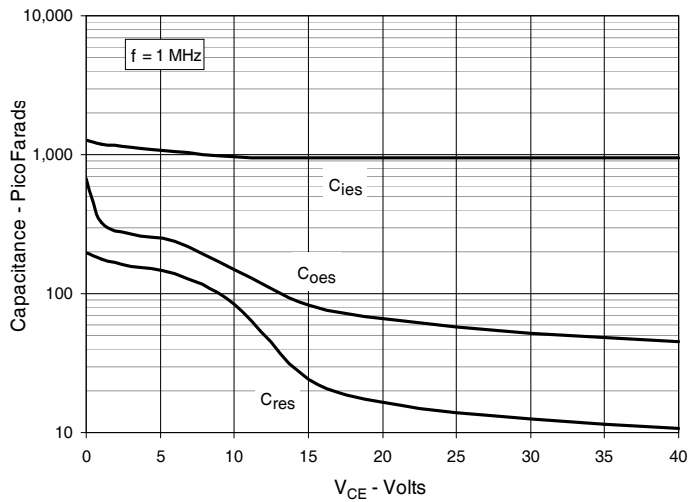


Fig. 10. Reverse-Bias Safe Operating Area

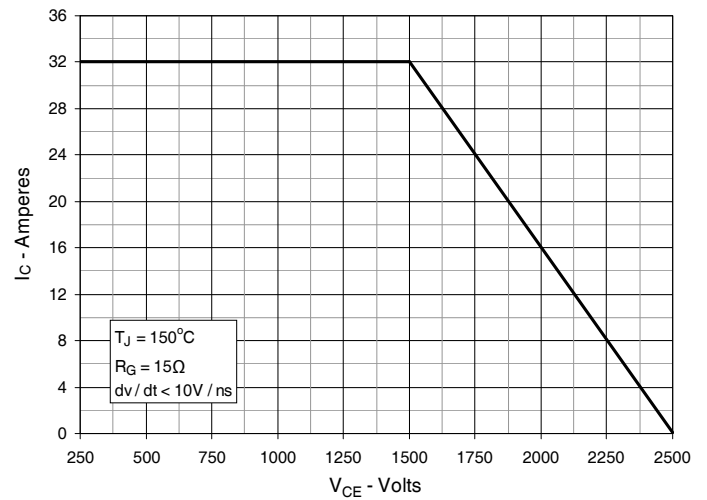


Fig. 11. Maximum Transient Thermal Impedance

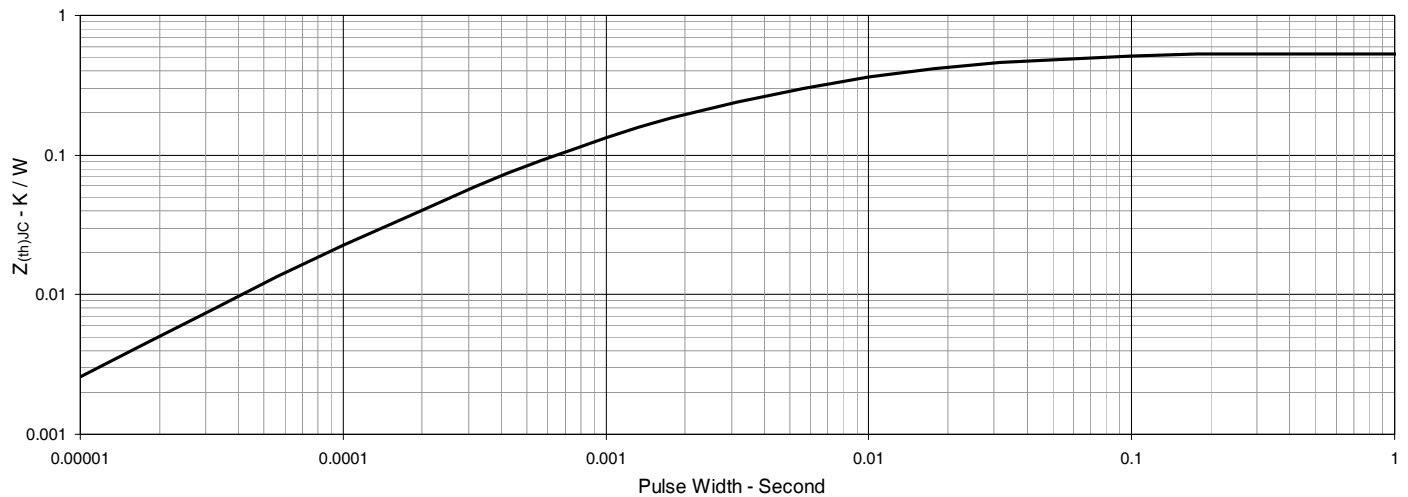


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

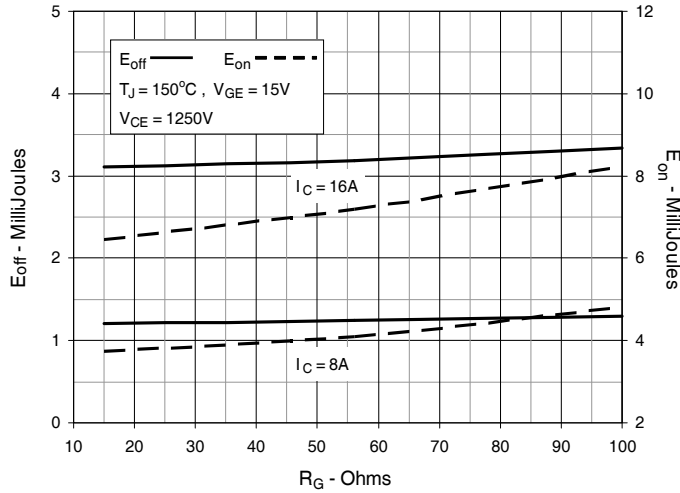


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

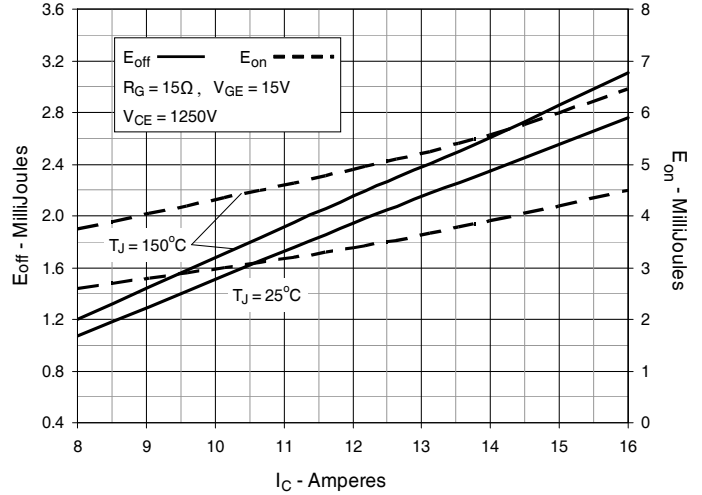


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

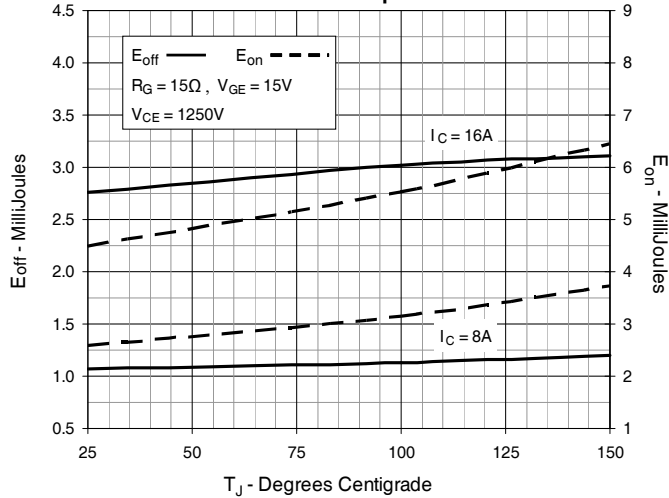


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

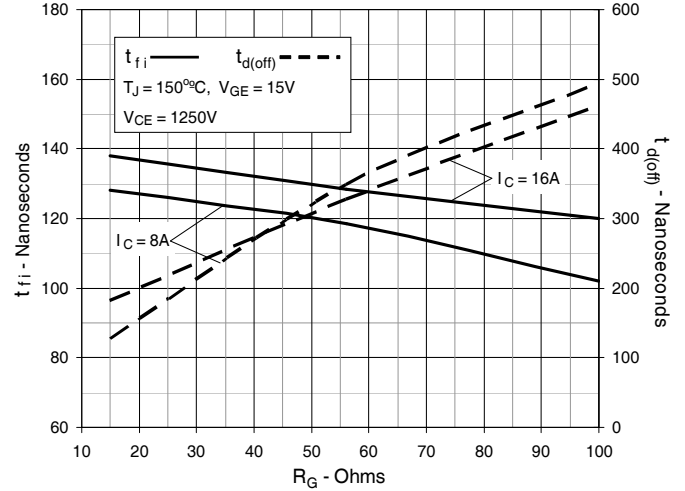


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

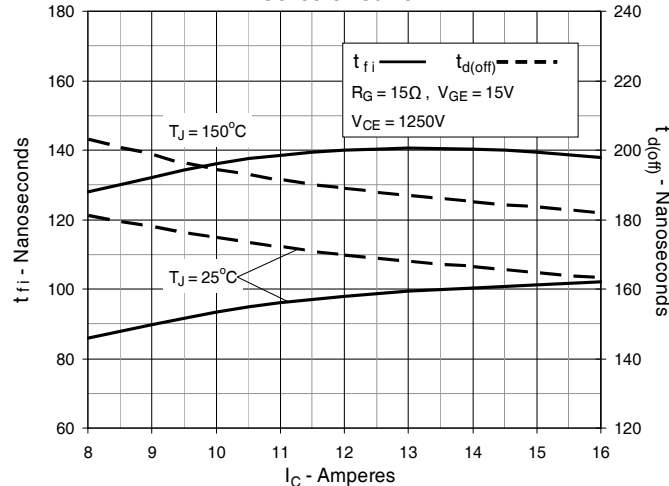


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

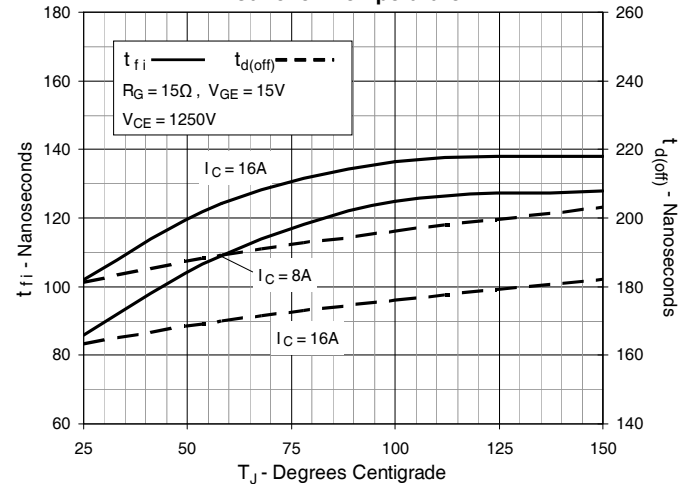


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

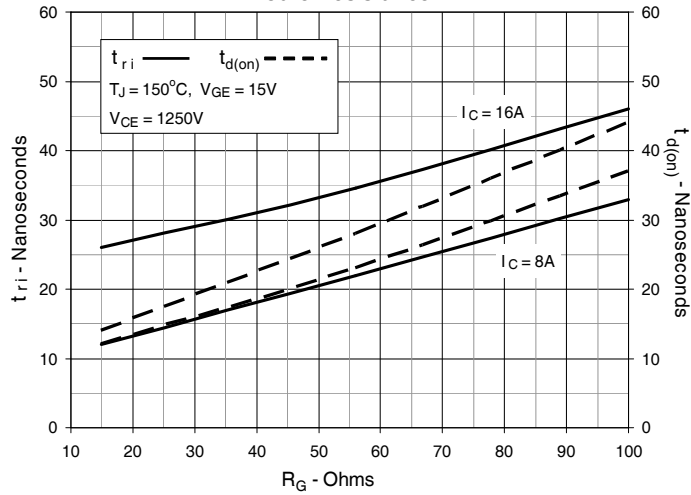


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

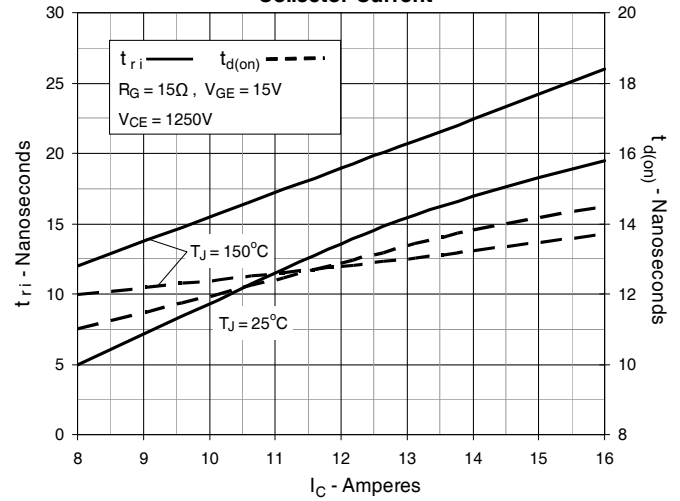
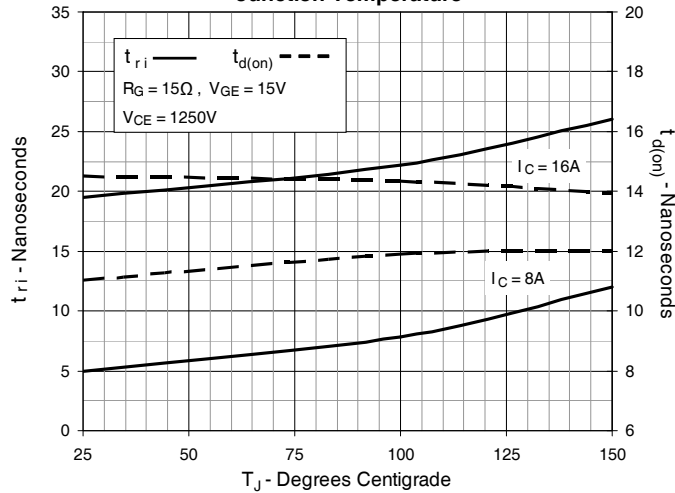


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.